

WAFER INCLUDING AN In-CONTAINING-COMPOUND SEMICONDUCTOR SURFACE LAYER, AND METHOD FOR PROFILING ITS CARRIER CONCENTRATION

Abstract of Disclosure

Method for non-invasively profiling carrier concentration in In-containing compound semiconductor wafers that enables employing the profiled wafers themselves in semiconductor device applications. The method, which using the C/V technique profiles carrier concentration in wafers including an In-containing-compound semiconductor surface layer, is characterized in non-invasively profiling carrier concentration by contacting a liquid electrode on the wafer surface, and without using photo-etching, employing an applied voltage that is up to a voltage surpassing 10V.